Silicon PNP Power Transistors 2SA1249

DESCRIPTION

·With TO-126 package
·Complement to type 2SC3117
·High breakdown voltage
·Large current capacity

APPLICATIONS

·For color TV sound output,converters,
Inverters applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

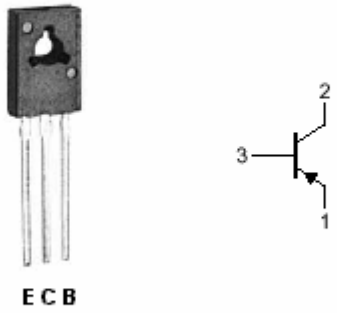

Fig.1 simplified outline (TO-126) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-180	V
V_{CEO}	Collector-emitter voltage	Open base	-160	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-1.5	A
I_{CM}	Collector current-Peak		-2.5	A
P_C	Collector power dissipation	T_a=25□	1.0	W
		T_C=25□	10	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-1mA; R_{BE}=∞		-160		V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-10μA; I_E=0		-180		V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-10μA ; I_C=0		-6		V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-500mA; I_B=-50mA		-0.2	-0.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-500mA; I_B=-50mA		-0.85	-1.2	V
I_{CBO}	Collector cut-off current	V_{CB}=-120V; I_E=0			-1.0	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-4V; I_C=0			-1.0	μA
h_{FE-1}	DC current gain	I_C=-100mA ; V_{CE}=-5V	100		400	
h_{FE-2}	DC current gain	I_C=-10mA ; V_{CE}=-5V	90			
f_T	Transition frequency	I_C=-50mA ; V_{CE}=-10V		120		MHz
C_{ob}	Output capacitance	I_E=0 ; V_{CB}=-10V;f=1MHz		22		pF

◆ **h_{FE-1} Classifications**

R	S	T
100-200	140-280	200-400

PACKAGE OUTLINE

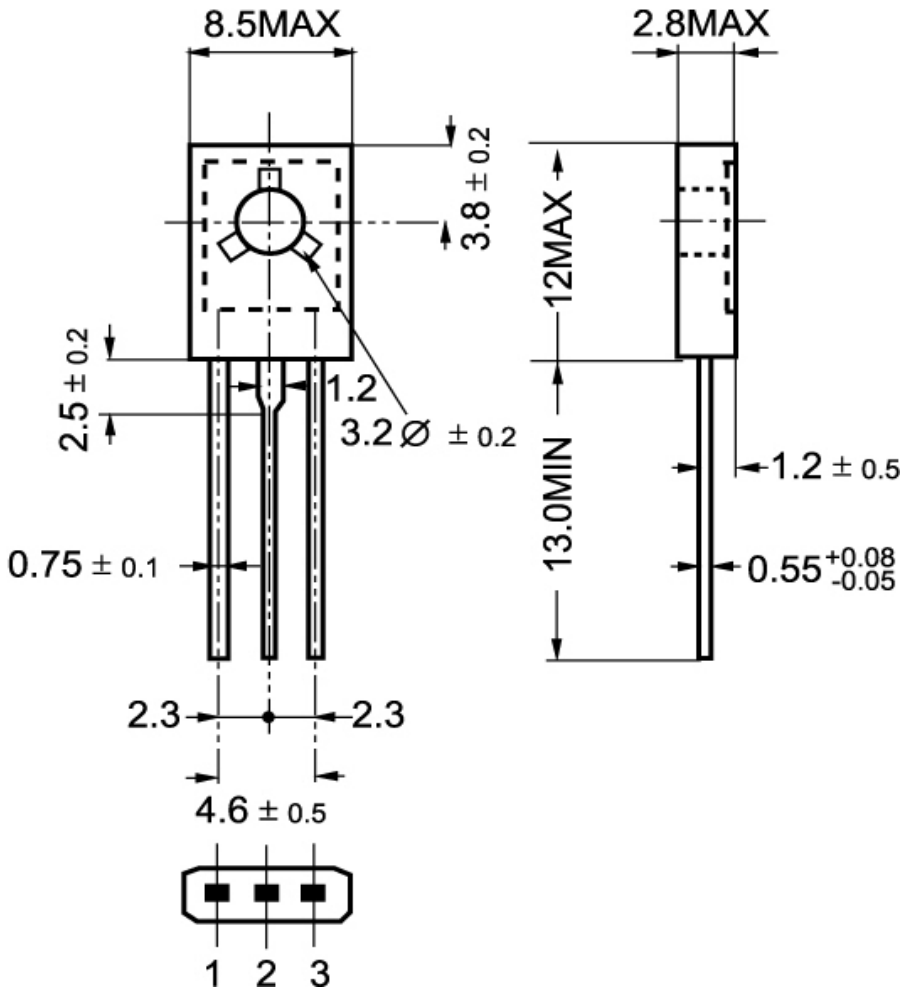

Fig.2 Outline dimensions

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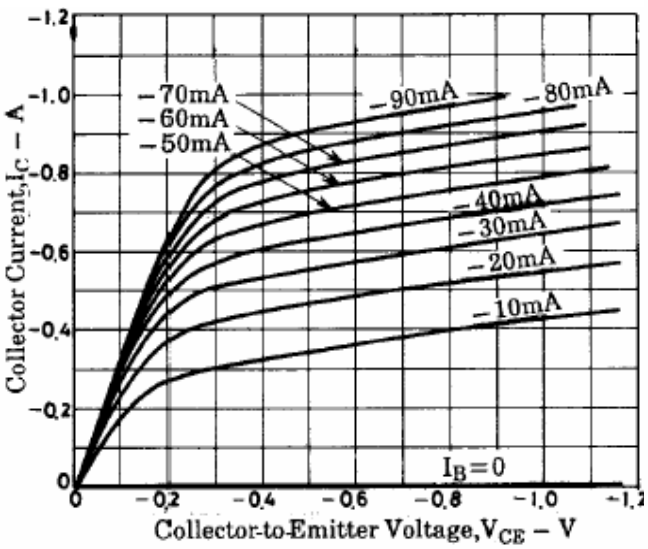

Fig.3 Static Characteristic

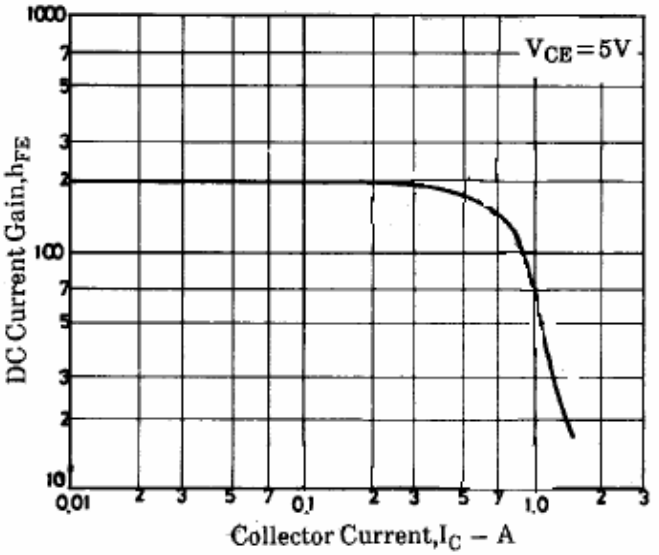

Fig.4 DC current Gain

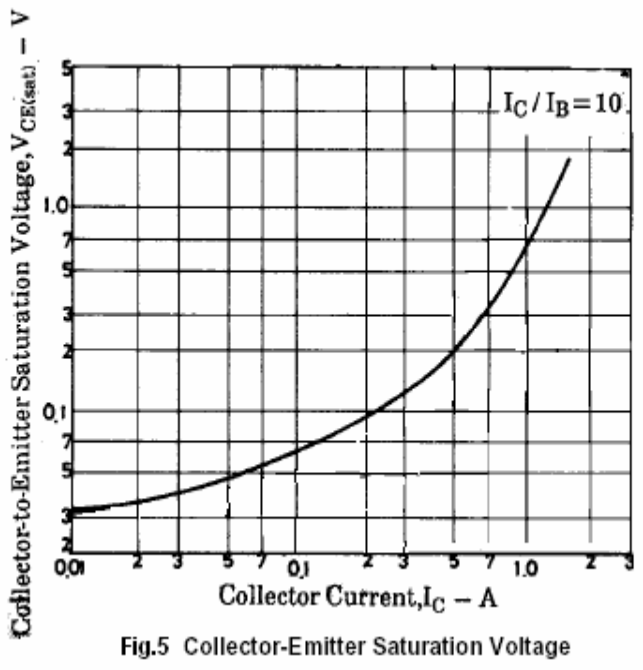

Fig.5 Collector-Emitter Saturation Voltage

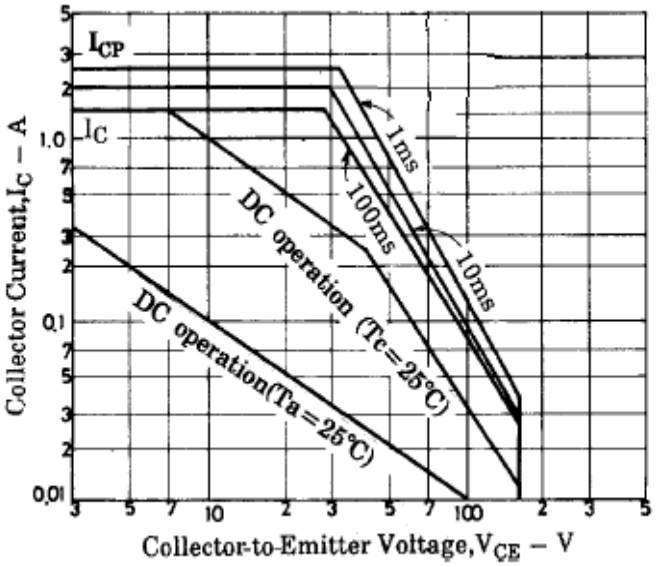

Fig.6 Safe Operating Area